

General Description

The HTS3005 is a dual, low on-resistance, low voltage, bidirectional, single-pole/doublethrow (SPDT) CMOS analog switch designed to operate from a single 1.8V to 5.5V power supply. Targeted applications include battery powered equipment that benefit from low Ron (0.5Ω) and fast switching speeds (ton = 50ns, toff = 15ns).

The on resistance profile is very flat over the full analog signal range. This ensures excellent linearity and low distortion when switching audio signals.

The HTS3005 is a committed dual single-pole/double-throw (SPDT) that consist of two normally open (NO) and two normally close (NC) switches. This configuration can be used as a dual 2-to-1 multiplexer.

HTS3005 is available in Green TDFN-3×3-10L and MSOP-10 packages.

Features

- Low Voltage Operation: 1.8V to 5.5V
- Low On-Resistance: 0.5Ω (TYP)
- Low On-Resistance Flatness
- -3dB Bandwidth: 15MHz
- Fast Switching Times:
 - ► ton 50ns
 - toff 15ns
- Rail-to-Rail Operation
- Typical Power Consumption (<0.01µW)
- TTL/CMOS Compatible
- Microsize Packages

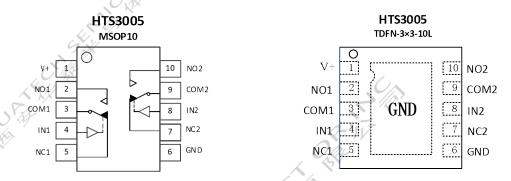
Application

- Battery-powered, Handheld, and Portable Equipment
 - Cellular/Mobile Phones
 - Laptops, Notebooks, Palmtops
- **Communication Systems**
- Sample-and-Hold Circuits
- **Audio Signal Routing**
- Audio and Video Switching
- Portable Test and Measurement
- Medical Equipment





Pin Configurations



Pin Description

Symbol	Description
V+	Power supply.
GND	Ground.
IN1, IN2	Digital control pin to connect the COM terminal to the NO or NC terminals.
COM1, COM2	Common terminal.
NO1, NO2	Normally-open terminal.
NC1, NC2	Normally-closed terminal.

Ordering Information

Type Number	Package Name	Package Quantity Marking Code
HTS3005XV10/R6	MSOP10	Tape and Reel,3000 C3005X
HTS3005XF10/R6	TDFN-3×3-10	Tape and Reel,3000 C3005X

Recommended Operating Conditions

- Operating voltage range: 1.8V to 5.5V
- Specified temperature range: -40°C to 125°C





Absolute Maximum Ratings

Attention: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

C 1/2			
Parameter	Symbol	Absolute Maximum Rating	Unit
	V+ to GND	-0.3V to 6V	V
355	Analog, Digital voltage range (1)	-0.3V to (V+) + 0.3V	V
C)	Continuous Current NO, NC, or COM	±300mA	mA
	Peak Current NO, NC, or COM	±500mA	mA
	Operating Temperature Range	-40°C to +125°C	°C
- ,	Storage	65°C to +150°C	°C
Temperature	Junction	150°C	°C
Package Thermal Resistance	TDFN-3×3-10L, θJA	33°C/W	°C/W
@ TA = 25°C	MSOP-10, θJA	205°C/W	°C/W
	Lead Temperature (soldering, 10s)	260°C	°C
ESD Susceptibility	HBM -	2000V	V
ESD Susceptibility	MM	400V	Q-11V

- (1) Signals on NC, NO, or COM exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- (2) Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





Electrical Characteristics

V+=+5V, GND = 0V, TA = -40 °C to +125 °C, typical values are at TA = +25 °C, unless otherwise noted

	C							
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
ANALOG SWITCH								
V_{NO}, V_{NC}, V_{COM}	Analog Signal Range	T _A =-40°C to + 125°C	0		$V_{\scriptscriptstyle +}$	V		
R _{ON}	On-Resistance	0 V_{NO} or V_{NC} V_{+} , $I_{COM} = -10$ mA, Test Circuit 1		0.5	0.9	Ω		
	<u></u>	T _A =-40°C to + 125°C		Qu'IV	1.1	Ω		
R _{on}	On-Resistance Match Between Channels	$0 V_{NO}$ or $V_{NC} V_{+}$, $I_{COM} = -10$ mA, Test Circuit 1		0.05	0.09	Ω		
		Ta=-40°C to + 125°C	24		0.12	Ω		
$R_{\text{FLAT(ON)}}$	On-Resistance Flatness	0 V _{NO} or V _{NC} V ₊ , I _{COM} = - 10mA, Test Circuit 1	×,7	0.25	0.3	Ω		
		Ta=-40°C to + 125°C			0.4	Ω		
LEAKAGE	E CURRENTS	10 KX						
I _{NC(OFF)} , I _{NO(OFF)}	Source OFF Leakage Current	V_{NO} or V_{NC} = 4.5V/1V, V_{COM} = 1V/4.5V, V_{+} = +5.5V, Test Circuit 2		±4	±10	nA		
	<u> </u>	T _A =-40°C to + 125°C			±1000	nA		
I _{NC(ON),} I _{NO(ON),}	Channel ON Leakage Current	V_{NO} or $V_{NC} = V_{COM} = 1V$ or 4.5V, $V_{+} = +5.5V$, Test Circuit 3		±4	±10	nA		
COM(ON),	J'AF	T _A =-40°C to + 125°C			±1000	nA		
DIGITAL	INPUTS					1		
V _{INH}	Input High Voltage	T _A =-40°C to + 125°C	2.4		. >			
V _{INL}	Input Low Voltage	T _A =-40°C to + 125°C			0.8	V		
I _{INL} or I _{INH}	Input Current	$V_{IN} = V_{INH}$ or V_{INL}		±0.01	±0.1	μΑ		
TINE TO TINE		T _A =-40°C to + 125°C)±1	μΑ		
DYNAMIC (CHARACTERISTICS			24	5			
t _{on}	Turn-On Time	V_{NO} or V_{NC} = 3V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4		50		nS		
t _{OFF}	Turn-Off Time	V_{NO} or V_{NC} = 3V, R_{L} = 300 Ω , C_{L} = 35pF, Test Circuit 4	/4/3	15		nS		
Q	Charge Injection	$C_L = 1.0 nF$, $V_G = 0V$, $R_G = 0\Omega$, Test Circuit 5	V-/L	20		рС		
t _D	Break-Before-Make Time Delay	V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 3V$, $R_L = 300\Omega$, $C_L = 35pF$, Test Circuit 6) (A) (5)	10		nS		
O _{ISO}	Off Isolation	$R_L=50\Omega$ $C_L=5pF$, Test $f=100kHz$		-70		dB		
		Circuit 7 f = 10kHz		-85		dB		



Electrical Characteristics

V+=+5V, GND = 0V, TA = -40 °C to +125 °C, typical values are at TA = + 25 °C, unless otherwise noted

Symbol	Parameter 2	Conditions M		Min.	Тур.	Max.	Unit
V	Channel-to-Channel Crosstalk	$R_L = 50\Omega$,	f = 100kHz		-90		dB
X _{TALK}		C _L = 5pF, Test Circuit 8	f = 10kHz		-105		dB
THD	Total Harmonic Distortion	f = 20Hz to 20kHz, V_{COM} = 3.5V _{P-P} , R_L = 600 Ω , C_L = 50pF			0.065		%
BW	-3dB Bandwidth	$R_L = 50\Omega$, $C_L = 5pF$, Test Circuit 9			115		MHZ
C _{NC(OFF)} , C _{NO(OFF)}	Source off Capacitance				80		pF
C _{NC(ON)} , C _{NO(ON)} , C _{COM(ON)}	Channel on Capacitance	Sx.			380		pF
POWER REQUIREMENTS							
I ₊	Power Supply Current	$V_{+} = +5.5V, V_{IN} = 0V \text{ or } 5V$		0.001		μΑ	
		T _A =-40°C to + 1	125°C			1	μΑ





Electrical Characteristics

V+=+3V, GND = 0V, TA = -40 °C to +125 °C, typical values are at TA = +25 °C, unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
ANALOG S	WITCH 5-X								
V_{NO}, V_{NC}, V_{COM}	Analog Signal Range	T _A =-40°C to + 125°C	0		$V_{\scriptscriptstyle +}$	V			
R _{on}	On-Resistance	0 V_{NO} or V_{NC} V_{+} , $I_{COM} = -10$ mA, Test Circuit 1		0.6	1.0	Ω			
1	>	T _A =-40°C to + 125°C		Car 111	1.3	Ω			
R _{on}	On-Resistance Match Between Channels	0 V _{NO} or V _{NC} V ₊ , I _{COM} = - 10mA, Test Circuit 1		0.05	0.1	Ω			
		T _A =-40°C to + 125°C	24		0.13	Ω			
$R_{\text{FLAT(ON)}}$	On-Resistance Flatness	0 V _{NO} or V _{NC} V ₊ , I _{COM} = - 10mA, Test Circuit 1	×	0.25	0.3	Ω			
		T _A =-40°C to + 125°C			0.4	Ω			
LEAKAGE	E CURRENTS	NO KY							
I _{NC(OFF)} , I _{NO(OFF)}	Source OFF Leakage Current	V_{NO} or $V_{NC} = 3V/1V$, $V_{COM} = 1V/3V$, $V_{+} = +3.3V$, Test Circuit 2		±5	±11	nA			
		T _A =-40°C to + 125°C			±1000	nA			
I _{NC(ON),} I _{NO(ON),}	Channel ON Leakage Current	V_{NO} or $V_{NC} = V_{COM} = 1V$ or $3V$, $V_{+} = +3.3V$, Test Circuit 3		±5	±11	nA			
ICOM(ON),	J'4	T _A =-40°C to + 125°C			±1000	nA			
DIGITAL	INPUTS					4			
V _{INH}	Input High Voltage	T _A =-40°C to + 125°C	2.0			O XX			
V_{INL}	Input Low Voltage	T _A =-40°C to + 125°C			0.4	V			
I _{INL} or I _{INH}	Input Current	$V_{IN} = V_{INH}$ or V_{INL}		±0.01	±0.1	μΑ			
INL - INFI	,	$T_A=-40$ °C to + 125°C			<u>±</u> 1	μΑ			
DYNAMIC (CHARACTERISTICS			74	*				
t _{on}	Turn-On Time	V_{NO} or V_{NC} = 2V, R_L = 300 Ω C_L = 35pF, Test Circuit 4	,	50		nS			
t _{OFF}	Turn-Off Time	V_{NO} or V_{NC} = 2V, R_L = 300 Ω , C_L = 35pF, Test Circuit 4	/4/3	17		nS			
Q	Charge Injection	$C_L = 1.0$ nF, $V_G = 0$ V, $R_G = 0$ Ω, Test Circuit 5	7-14	25		рС			
t _D	Break-Before-Make Time Delay	V_{NO1} or $V_{NC1} = V_{NO2}$ or V_{NC2} = 2V, R _L = 300 Ω , C _L = 35pF, Test Circuit 6) (M %)	11		nS			
O _{ISO}	Off Isolation	$R_L=50\Omega$ $C_L=5pF$, Test	-	-70		dB			
		Circuit 7 f = 10kHz		-85		dB			



Electrical Characteristics

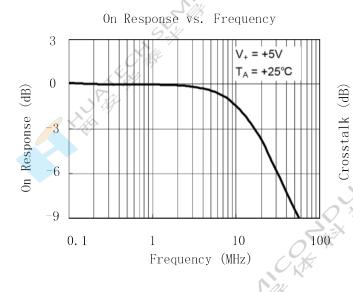
V+ = +5V, GND = 0V, TA = -40 $^{\circ}$ C to +125 $^{\circ}$ C, typical values are at TA = + 25 $^{\circ}$ C, unless otherwise noted

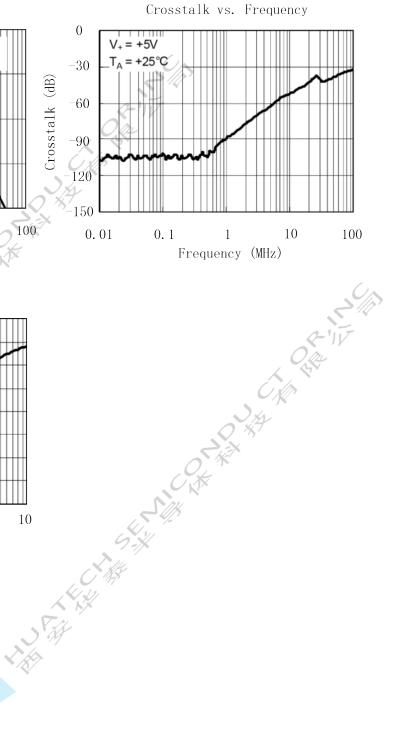
Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
V	Channel-to-Channel	$R_L = 50\Omega$,	f = 100kHz		-90		dB
X_{TALK}	Crosstalk	C _L = 5pF, Test Circuit 8	f = 10kHz		-105		dB
THD	Total Harmonic Distortion	f = 20Hz to 20kHz, V_{COM} = 2VP-P, R_L = 600 Ω , C_L = 50pF			0.06		%
BW	-3dB Bandwidth	$R_L = 50\Omega$, $C_L = 5pF$, Test Circuit 9			1115		MHZ
C _{NC(OFF)} ,	Source off Capacitance	A ANG			80		pF
C _{NC(ON)} , C _{NO(ON)} , C _{COM(ON)}	Channel on Capacitance			NA NA	380		pF
POWER REQUIREMENTS							
I ₊	Dower Supply Current	$V_{+} = +3.3V, V_{\parallel}$	_N = 0V or 5V		0.001		μΑ
	Power Supply Current	T _A =-40°C to +	125°C			1	μΑ

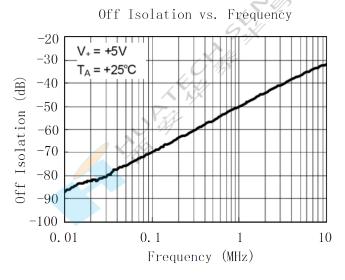




Type Performance Characteristics

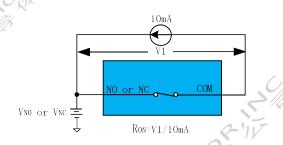




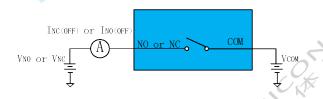


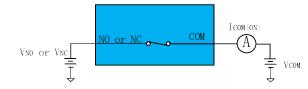


Application Notes



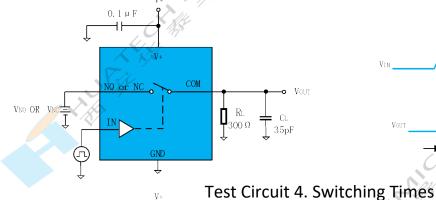
Test Circuit 1. On Resistance

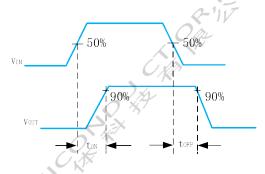


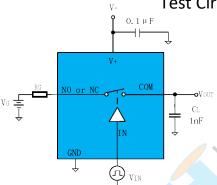


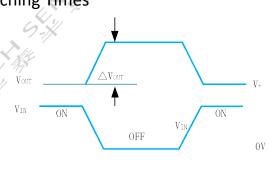
Test Circuit 2. Off Leakage

Test Circuit 3. On Leakage





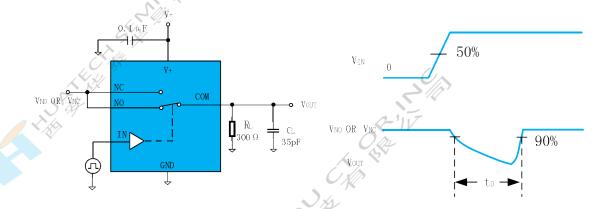




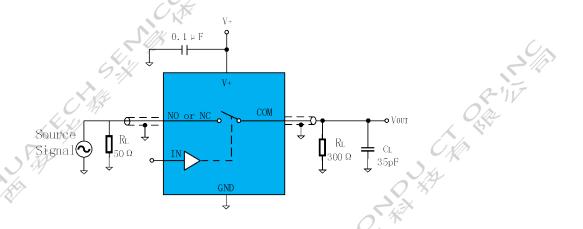
Test Circuit 5. Charge Injection



Application Notes



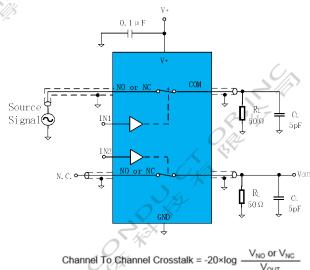
Test Circuit 6. Break-Before-Make Time Delay, tD



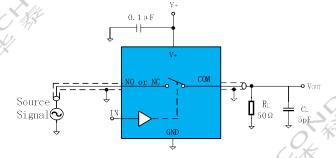
Test Circuit 7. Off Isolation



Application Notes



Test Circuit 8. Channel-to-Channel Crosstalk

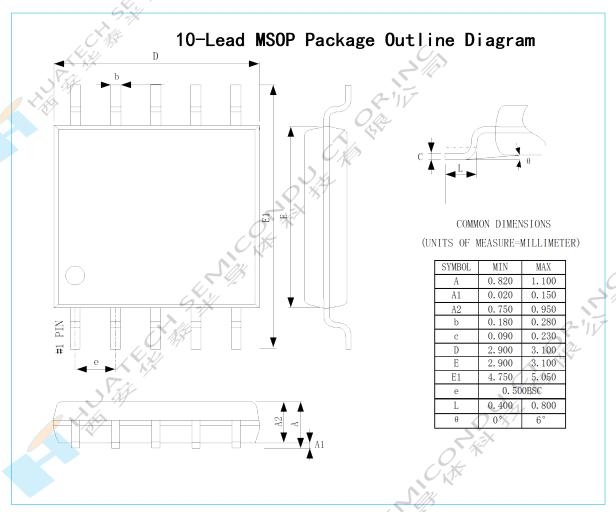


Test Circuit 9. -3dB Bandwidth



Package Outlines







Package Outlines

TDFN-3×3-10L

